**Product data sheet** 

## 1. General description

Planar passivated ultra sensitive gate Silicon Controlled Rectifier in a SOT223 surface mountable plastic package.

#### 2. Features and benefits

- · Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate
- Surface mountable package

## 3. Applications

- Electronic ballasts
- · Safety shut down and protection circuits
- Sensing circuits
- · Smoke detectors
- Switched Mode Power Supplies

#### 4. Quick reference data

Table 1. Quick reference data

	R reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	400	V
$I_{T(AV)}$	average on-state current	half sine wave; T <sub>sp</sub> ≤ 114 °C; <u>Fig. 1</u>	-	-	0.5	Α
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{sp} \le 114 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3	-	-	0.8	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	-	8	Α
		half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 8.3 ms	-	-	9	Α
$T_j$	junction temperature		-	-	125	°C
Static chara	cteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$	-	3	12	μA
Dynamic cha	aracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 268 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	_	150	-	V/µs

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# **5. Pinning information**

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	4	А <del>-    </del> К
2	Α	anode		G sym037
3	G	gate		symosi
4	mb	mounting base; connected to anode	☐1 ☐2 ☐3 SC-73 (SOT223)	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
EC103D1W	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

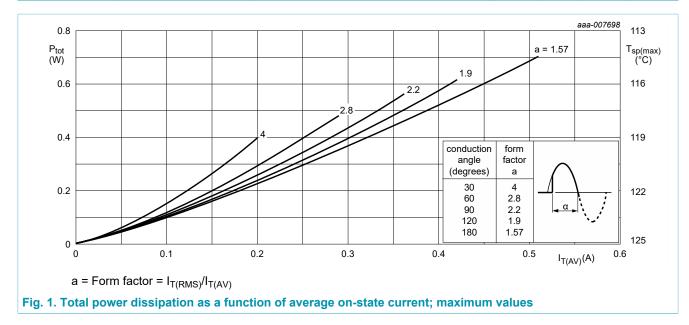
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# 7. Limiting values

## **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	400	V
$V_{RRM}$	repetitive peak reverse voltage		-	400	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>sp</sub> ≤ 114 °C; <u>Fig. 1</u>	-	0.5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>sp</sub> ≤ 114 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	0.8	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	8	Α
		half sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 8.3 ms	-	9	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	0.32	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 2 \text{ A}$ ; $I_G = 0.01 \text{ A}$ ; $dI_G/dt = 0.1 \text{ A}/\mu\text{s}$	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	1	Α
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



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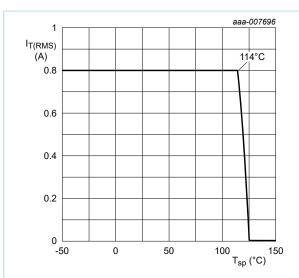


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

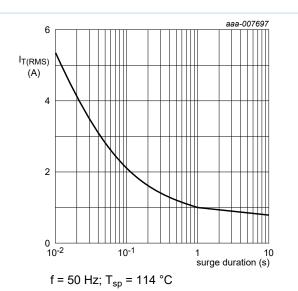


Fig. 3. RMS on-state current as a function of surge duration; maximum values

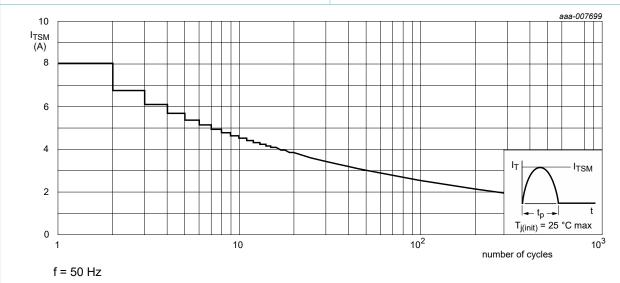
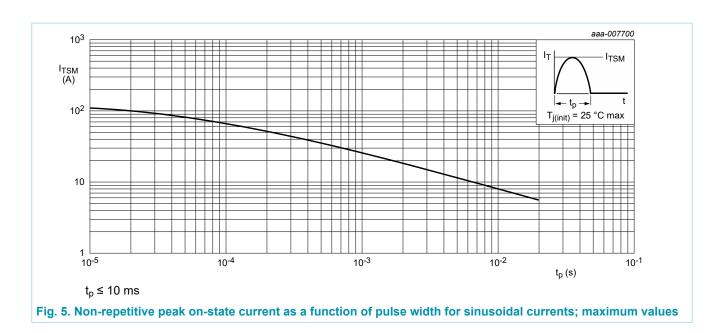


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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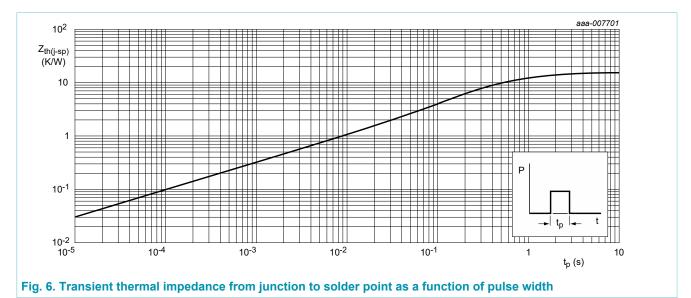


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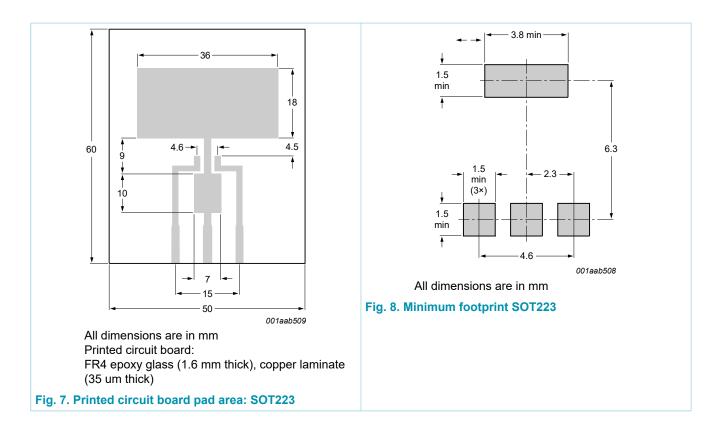
#### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	Fig. 6	-	-	15	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to	printed circuit board mounted; minimum pad area; in free air; Fig. 7	-	70	-	K/W
	ambient free air	printed circuit board mounted; minimum footprint; in free air; Fig. 8	-	156	-	K/W



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## 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					_
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	3	12	μA
lL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 10	-	2	6	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	2	5	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.2	1.35	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	-	0.5	0.8	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 13	0.2	0.3	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C	-	0.05	0.1	mA
I <sub>R</sub>	reverse current	V <sub>R</sub> = 400 V; T <sub>j</sub> = 125 °C	-	0.05	0.1	mA
Dynamic ch	naracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 268 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	-	150	-	V/µs

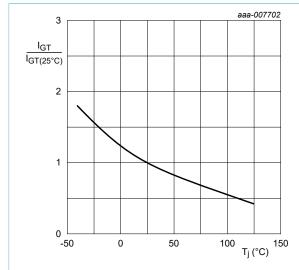


Fig. 9. Normalized gate trigger current as a function of junction temperature

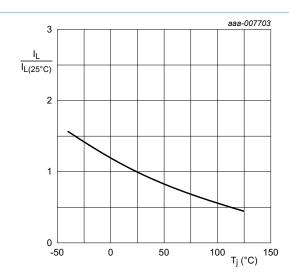


Fig. 10. Normalized latching current as a function of junction temperature

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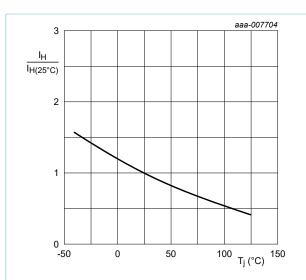
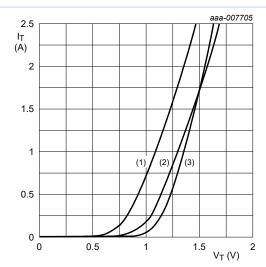


Fig. 11. Normalized holding current as a function of junction temperature



 $V_o = 0.987 \text{ V}; R_s = 0.3125 \Omega$ 

(1)  $T_j = 125$  °C; typical values (2)  $T_j = 125$  °C; maximum values

(3)  $T_j = 25$  °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

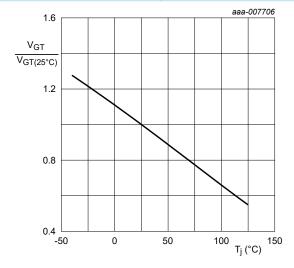
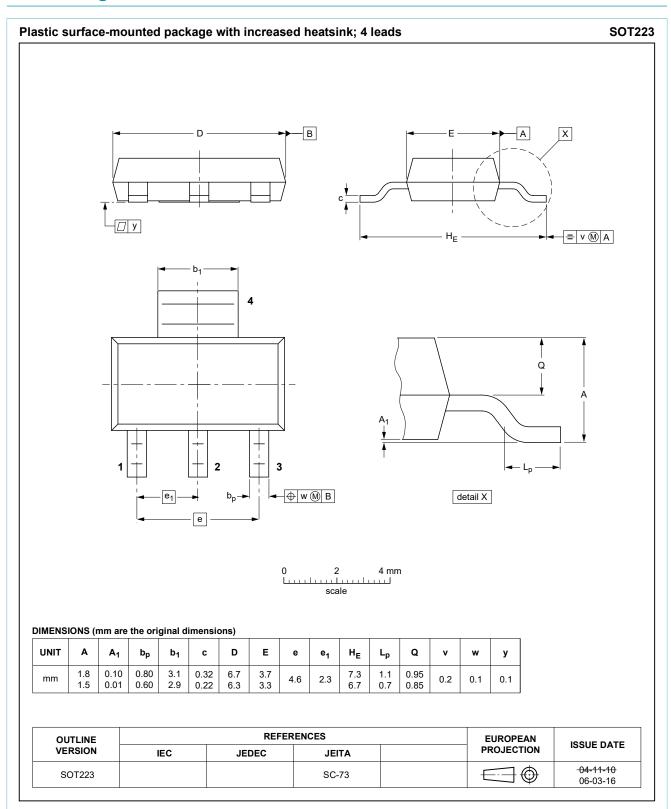


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

## 10. Package outline



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## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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EC103D1W

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Date of release: 21 August 2018

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